Notice of Allowability	Application No.	Applicant(s)
	10/716,606	HIMI ET AL.
	Examiner	Art Unit
	Thanhha Pham	2813
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. X This communication is responsive to 10/31/2006 and in terview dated 1/16/2007.		
2. The allowed claim(s) is/are <u>1-3,5 and 30</u> .		
 3. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some* c) None of the: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		
4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
5. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.		
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached		
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date		
Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).		
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.		
	·	
Attachment(s)		
1. Notice of References Cited (PTO-892)	5. Notice of Informal P	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary (PTO-413), Paper No./Mail Date	
3. ☑ Information Disclosure Statements (PTO/SB/08), 7. ☑ Examiner's An Paper No./Mail Date 10/102006		
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. ⊠ Examiner's Statement of Reasons for Allowance 9. □ Other	
	THANHI PRIMAR)	

Application/Control Number: 10/716,606 Page 2

Art Unit: 2813

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Kerry Culpepper on 01/16/2007.

The application has been amended as follows:

In claim 1,

line 6, after "atmosphere" insert -- , the insulating layer is formed in a such manner that the insulating layer has a thickness of about one hundred nanometers and a stratiform region of the insulating layer at the interface between the epitaxial layer and the semiconductor substrate is provided --

- Cancel claims 15-29
- Cancel claim 32

Allowable Subject Matter

- 1. Claims 1-3 and 5 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: Recorded Prior Art fails to disclose or suggest the combination of the process steps of method for manufacturing a semiconductor substrate as recited in the base claim 1 including forming an insulating layer by deposition at an interface between the epitxial layer and

Art Unit: 2813

the semiconductor substrate by performing a heat treatment that is performed in an oxidizing atmosphere, the insulating layer is formed in a such manner that the insulating layer has a thickness of about one hundred nanometers and a stratiform region of the insulating layer at the interface between the epitaxial layer and the semiconductor substrate is provided, wherein the heat treatment for forming the insulating layer is performed at a temperature higher than about 1100oC; the insulating layer is formed from a distortion layer as nuclei disposed at the interface between the epitaxial layer and the semiconductor substrate and the distortion layer is formed by a difference of impurity concentration or a lattice constant between the epitaxial layer and the semiconductor substrate.

3. Claim 1 is allowable. The restriction requirement, as set forth in the Office action mailed on 11/28/2004, has been reconsidered in view of the allowability of claims to the elected invention pursuant to MPEP § 821.04(a). The restriction requirement is hereby withdrawn as to any claim that requires all the limitations of an allowable claim. Claim 5 is no longer withdrawn from consideration because the claim(s) requires all the limitations of an allowable claim. However, claims 15-29, directed to non-species withdrawn from consideration because they do not require all the limitations of an allowable claim. Accordingly, claims 15-29 have been cancelled.

In view of the above noted withdrawal of the restriction requirement, applicant is advised that if any claim presented in a continuation or divisional application is anticipated by, or includes all the limitations of, a claim that is allowable in the present

Application/Control Number: 10/716,606

Art Unit: 2813

application, such claim may be subject to provisional statutory and/or nonstatutory double patenting rejections over the claims of the instant application.

Once a restriction requirement is withdrawn, the provisions of 35 U.S.C. 121 are no longer applicable. See *In re Ziegler*, 443 F.2d 1211, 1215, 170 USPQ 129, 131-32 (CCPA 1971). See also MPEP § 804.01.

- 4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."
- 5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanhha Pham whose telephone number is (571) 272-1696. The examiner can normally be reached on Monday and Thursday 9:00AM 9:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

Art Unit: 2813

you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TSP

THANHHA S. PHAM PRIMARY EXAMINER